The Compensation Law for Conductivity of Ionic Crystals

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The conductivity prefactor A is specified as a function of the conductivity activation energy E_A for a large series of alkali halide type crystals and of superionic conductors (SIC). A linear dependence of the form $\log A = 2.1E_A + 5.3$ is observed for classical ionic conductors (CIC) with values of $E_A > 0.9$ eV, as well as for SIC with $E_A > 0.4$ eV. Such behavior, known as the compensation law (CL) cannot be understood within the framework of the conventional assumption of temperature-dependent E_A values. It is demonstrated that the CL is characteristic for defect formation as well as for defect migration processes, with corresponding isokinetic temperatures $T_0 = 2.8 \times 10^3$ K and $T_{\mu} = 2.1 \times 10^3$ K, respectively. For lower values of $E_A (E_A < 0.9 \text{ eV}$ for CIC and $E_A < 0.4 \text{ eV}$ for SIC) a considerable decrease in the prefactor is observed. This is interpreted in terms of melting or positional disordering of mobile ions in the cation sublattice of the crystals. It is demonstrated that the conventional practice of using as the jump attempt frequency ν_0 the Debye frequency ν_D for the mobile ion seems to be invalid. We propose to use instead the expression suggested by Rice and Roth: $\nu_0 = (1/\pi) \cdot \sqrt{2H_{\mu}/a^2m}$.

The nonempirical solution to the problem of a directed search for new solid electrolytes cannot be attained without understanding (at least at the "Rule-of-Thumb" level) the peculiarities of different classes of ionically conducting crystals. The ion migration process in classical ionic solids may be described in terms of the simple hopping model. In the case of superionic conductors (SIC) the ion conduction mechanism is not yet known. Formally in both cases the temperature dependence of conductivity $\sigma(T)$ is known from experience to be reasonably well described by the Arrhenius equation

$$\sigma T = A \cdot \exp(-E_A/kT), \qquad (1)$$

where T is the temperature in K, k is Boltzmann's constant, E_A is the activation energy, and A is the conductivity prefactor.

For ionic solids of the NaCl type typical values of activation energy and those of prefactors lie in the range 1.0-2.5 eV and 10^7 - 10^{11} S · K/cm, respectively. The conductivity values at $T = 300^{\circ}$ C change from 10^{-10} to 10^{-3} S/cm. For SIC, E_A and A values remain in the range 0.05-0.4 eV and $10^3 - 10^6$ S · K/cm, respectively, the values of σ at $T = 300^{\circ}$ C being equal to 10^{-2} -10⁰ S/cm(1, 2). It is not clear how to classify the crystals characterized by defect concentrations as high as those in SIC (1-10 mole%) and by activation energies as high as 0.4-1.0 eV. Until lately no thorough studies of the conductivity prefactor in SIC were published, though a considerable body of data permit such an investigation to be carried out.

It has been observed that linear depen-

	E.	$\log A$ $(\mathbf{S} \cdot \mathbf{K})$			E_	$\log A$ (S · K)	
Salt	(eV)	(<u> </u>	Ref.	Salt	(eV)	(<u></u>)	Ref.
LiF	2.07	9.78	11	CsBr	1.44	8.1	14
LiCl	1.47	9.28	12	CsI	1.43	8.0	14
LiBr	1.29	9.00	12	CsNO ₃	1.05	7.7	14
LiI	0.96	7.2	13	TICI	0.87	6.95	14
LiN ₃	1.87	10.1	14	TlBr	0.785	5.97	22
NaF	2.2	9.7	15	α-TlI	0.68	5.34	22
NaCl	2.18	10.3	16	AgCl	0.99	7.6	14
NaBr	1.68	8.3	14	AgBr	0.87	7.8	14
NaI	1.66	9.26	17	α-AgI	0.97	6.8	14
NaNO ₂	1.15	7.8	14	AgN_3	0.82	7.0	14
NaN ₃	1.82	9.8	14	β-CaF ₂	2.13	11	14
KF	2.34	10.0	14	β -SrF ₂	2.14	9.75	14
KCl	2.36	10.75	14	β-SrCl ₂	1.25	7.3	14
KBr	2.21	9.85	14	β-BaF₂	1.64	8.83	14
KI	1.93	9.40	18	CdCl ₂	1.03	8.0	14
RbCl	1.59	8.6	19	PbCl ₂	0.89	6.1	14
RbBr	2.02	9.50	20	PbBr ₂	0.71	4.7	14
RbI	2.16	9.54	21	PbI ₂	1.3	5.3	14
CsF	1.55	8.2	14	CuSO₄	2.21	10.1	14
α-CsCl	1.67	8.0	14	γ -SnF ₂	0.74	6.3	23
β-CsCl	1.33	7.9	14	β -PbF ₂	0.45	4.8	24

TABLE I

EXPERIMENTAL DATA ON IONIC CONDUCTIVITY OF ORDINARY IONIC CRYSTALS

dences between log A and E_A are encountered in some groups of crystals (3-5). A similar dependence between D_0 and E_D is known for metals (6), where E_D is the activation energy for the self-diffusion and D_0 is its preexponential factor. Such a relationship is likely to be characteristic of diffusion-controlled reactions and is known as the compensation law (CL) (4-7). While some explanations of the CL (7, 9) have been provided, no real theory of the law has so far been proposed.

In this paper an attempt is made to obtain quantitative correlations between the values of log A and E_A in the alkali halides (AH), in some other inorganic crystals as well as in SIC, and to apply these correlations to the analysis of the conductivity mechanism in the above-mentioned ionic solids.

Alkali Halide-Type Crystals

The ionic conductivity of AH type crystals has been intensively investigated. However, the considerable discrepancy in values of E_A and A cited by different authors raise many questions concerning the earlier CL studies in AH type crystals. According to Dosdale and Brook (10) a CL in conductivity is observed for the same crystals when measurements are carried out in different parts of the region intermediate between the intrinsic and extrinsic regions of conductivity. According to the authors, the correct A and E_A values are the highest ones obtained in a series of independent measurements made for the same compound. Such values for AH and for other ionic crystals are presented in Table I, taken from previous investigations of dif-



FIG. 1. The compensation law for conductivity of ionic crystals. Full and dashed lines are computed on the basis of Eqs. (2) and (11), respectively. Apparent deviations from the straight-line correlation are seen for $E_A < 0.9$ eV.

ferent authors. The experimental values with activation energies exceeding 0.9 ± 0.1 eV satisfied reasonably well a linear dependence of the type

$$\log A = (5.3 \pm 0.3) + (2.1 \pm 0.2) \cdot E_{\rm A},$$
(2)

where E_A is measured in eV and A in S \cdot K/ cm. The variation (2) is shown in Fig. 1. It is to be noted that the conductivity prefactor for some silver, lead, tin, and thallium salts with the conductivity activation energies not exceeding 0.9 ± 0.1 eV seems to be abnormally low.

We now analyze the prefactor A in detail. The volume concentration of defects (n) and the mobility of these defects (μ) being two factors in the expression for ionic conductivity $\sigma = q \cdot n \cdot \mu$ (where q is the defect charge) are known to depend exponentially on the reciprocal temperature:

$$n = N \exp(-H_0/kTz) \tag{3}$$

$$\mu = M \exp(-H_{\mu}/kT), \qquad (4)$$

where H_0 and H_{μ} are the enthalpy of defect formation and the free enthalpy of defect migration, respectively, and z is the number of species taking part in the quasichemical reaction of defect formation. The compensation law may arise either from that for defect formation or from that for the defect migration process, i.e., as a consequence of the dependence of N or M on H_0 or H_{μ} , respectively. Assuming H_{μ} and H_0 values to be temperature independent one can write for N and M (25):

$$N = N_0 \exp(S_0/zk) \tag{5}$$

$$M = (\gamma q a^2 \nu_0) / kT \cdot \exp(S_{\mu} / k), \qquad (6)$$

where N_0 is the total number of ions in 1 cm³ of a crystal, γ is the steric factor, a is the hopping distance, ν_0 is an attempt frequency to overcome the potential barrier, S_0 and S_{μ} are the entropies for defect formation and migration, respectively. If we suppose the defect formation as well as the defect migration enthalpies to decrease linearly with temperature (8) as: $H_0 = H'_0(1 - 1)$ $\alpha_1 T$), $H_{\mu} = H'_{\mu}(1 - \alpha_2 T)$, where H'_0 and H'_{μ} are the corresponding values at T = 0 K, the N and M values increase by the factors $\exp(H_0\alpha_1/zk)$ and $\exp(H_\mu\alpha_2/k)$, respectively. Assuming $\alpha_1 \cong \alpha_2 = \alpha$ for the case of AH type crystals, when z = 2, $\gamma = 4$ and E_A = $H_0/2$ + H_{μ} the prefactor A should be equal to

$$\log A = \log(N_0 4q^2 a^2 \nu_0 / k) + (S_0 / 2 + S_\mu + \alpha E_A) / 2.3k.$$
(7)

From comparison of Eq. (7) with the empirical relation given by Eq. (2) the values of $log(N_04q^2a^2\nu_0/k) + (S_0/2 + S_\mu)/2.3k$ and of $\alpha/2.3k$ would be equal to 5.3 ± 0.3 and to 2.1 ± 0.2 1/eV, respectively. The first term in Eq. (7) changes weakly in a series of AH type crystals and for the typical values of $\nu_0 = 3 \times 10^{12} \text{ s}^{-1}$, $a = 3 \times 10^{-8}$ cm, $N_0 = 10^{22} \text{ cm}^{-3}$ is equal to 5.2. In such a case both S_0 and S_μ would be nearly equal to zero and the CL is caused entirely by the temperature dependence of the activation energies. Theoretical estimates show, how-

TABLE II

ENTHALPIES AND ENTROPIES OF THE DEFECT FORMATION H_0 , S_0 and of the Defect Migration H_{μ} , S_{μ} , S_{μ}^* (S_{μ}^* Were Estimated at $\nu_0 = \nu_{\odot}$, S_{μ} Are Reestimated by Us Assuming that $\nu_0 = \nu_{\rm h}$) IN Ordinary Ionic Crystals

Salt	<i>H</i> ₀ (eV)	S ₀ /k	Defect type	H_{μ} (eV)	S_{μ}^{*}/k	S _µ /k	Ref.
 LiI	1.06	4.5	V 11	0.43	_		13
NaF	2.5	9.4	VNa	0.95	_	_	15
NaCl	2.44	9.8	VNa	0.69	1.64	2.9	29
			Vn	0.77	1.38	3.0	29
NaBr	1.78	4.68	V _{Na}	0.79	4.26	5.6	30
			VBr	1.25	7.25	8.5	36
NaI	2.00	7.64	V _{Na}	0.58	3.23	4.0	17
			V ₁	0.77	2.91	2.9	17
KCl	2.59	9.61	Vĸ	0.73	2.70	4.0	31
			\mathbf{V}_{Cl}	0.99	4.14	5.0	31
KBr	2.53	10.3	Vĸ	0.65	1.89	3.1	32
			VBr	1.22	7.30	8.6	32
KI	2.21	8.87	Vĸ	0.63	1.58	2.4	31
			VI	1.29	9.33	9.8	31
RbCl	2.44	_	V _{Rb}	0.54	1.73	3.3	33
AgCl	1.46	5.44	V _{Ag}	0.28	-0.48	1.4	34
AgBr	1.13	6.55	VAg	0.32	1.16	2.7	35
TICI	1.25	6.3	VTI	0.38	2.04	2.6	36
			V_{Cl}	0.10	-2.21	-0.3	36
β-CaF ₂	2.72	4.9	VF	0.43	1.6	3.2	37
			\mathbf{F}_{i}	0.78	4.5	5.8	37
β-BaF ₂	1.85	3.5	VF	0.55	3.4	3.8	37
			\mathbf{F}_{i}	0.73	4.5	4.8	37
β-SrF ₂	2.39	4.1	VF	0.55	3.4	4.4	37
			\mathbf{F}_{i}	0.75	2.8	3.7	37
β -PbF ₂	1.07	4.1	VF	0.23	1.1	1.9	37
			\mathbf{F}_{i}	0.5	4.2	3.6	37
β-SrCl₂	1.97	3.3	V_{Cl}	0.4	1.0	2.4	37

ever, that both defect formation and defect migration processes cause a considerable entropy change (26, 27). Therefore it is reasonable to suppose that values of H_0 and H_{μ} are only weakly dependent on (or entirely independent of) temperature and that the CL must be explained by the existing linear dependences of the type

$$S_0 = H_0/T_0$$
 (8)

$$S_{\mu} = H_{\mu}/T_{\mu}, \qquad (9)$$

where T_0 and T_{μ} are some so-called isokinetic temperatures.

For the estimation of S_{μ} from experimental data the Debye frequency $\nu_{\rm D}$ is generally used. After Rice and Roth (28) we consider that it is more reliable to take as ν_0 the quantity

$$\nu_{\rm h} = (1/\pi) \cdot \sqrt{2H_{\mu}/a^2m}$$
 (10)

which is valid for an ion moving in harmonic potential, *m* being the ion mass. In Table II the values of H_0 , H_{μ} , S_0 , S_{μ}^* , and S_{μ} are presented where S_{μ}^{*} is obtained for $\nu_{\rm D} = \nu_0$ and S_{μ} is estimated for $\nu_{\rm h} = \nu_0$. As is seen from Fig. 2 the S_0 values change linearly with H_0 . As for mobility, S_{μ} becomes linearly correlated with H_{μ} when $\nu_{\rm h}$ is used in place of $\nu_{\rm D}$ (see Figs. 3a and b). The mean values of isokinetic temperatures T_0 and T_{μ} are equal to 2.8 \times 10³ and 2.1 \times 10³ K, respectively. The mean value of T_0 for fluorite-type crystals seems to be higher than for AH type crystals. Assuming $H_{\mu} =$ $0.3H_0$ (38) for AH type crystals from Eqs. (8), (9), and (10) one can obtain the relation

$$\log A = \log \left(\frac{N_0 q^2 a \sqrt{0.75}}{\pi k \sqrt{m}} \sqrt{E_A} \right) + E_A (0.27/kT_0 + 0.16/kT_\mu). \quad (11)$$

As seen from Fig. 1 the calculated dependence (11) with $N_0 = 10^{22}$ cm⁻³, $a = 3 \times$



FIG. 2. The compensation law for the defect formation reaction in NaCl-type crystals (1) and in fluoritetype crystals (2). These data obey Eq. (8) with $T_0 = 2.8 \times 10^3$ K (AH crystals), 6.1×10^3 K (CaF₂-type crystals).



FIG. 3. The correlation between the entropy of migration S_{μ} and the activation enthalpy for mobility H_{μ} in ionic crystals. (a) S_{μ} calculated on the assumption $\nu_0 = \nu_D$; physically unacceptable negative S_{μ} cause deviations from linear dependence. (b) S_{μ} calculated using $\nu_0 = \nu_h = (1/\pi a)(2H_{\mu}/m)^{1/2}$. The slope of the improved straight-line fit yields $T_{\mu} = 2.1 \times 10^3$ K.

 10^{-8} cm, $m = 4 \times 10^{-23}$ g, $T_0 = 2.8 \times 10^3$ K, $T_{\mu} = 2.1 \times 10^3$ K is in accord with the experimentally observed one for AH type crystals having activation energies $E_A > 0.9$ ± 0.1 eV. The dependence (11) is in qualitative agreement with the experimentally observed abnormal decrease of A values for compounds having small activation energies. However, there are considerable quantitative discrepancies between the calculated and experimentally observed relations in the low-value region of E_A . For a careful analysis of the CL in this region of E_A a survey of conductivity data for SIC must be made.

Superionic Conductors

A compilation of experimental data on the ionic conductivites of SIC is presented in Table III. The principal difference of SIC from classical ionic conductors is assumed to be the high defect concentration $n = N_0$ in crystal lattice of SIC. For this case $H_0 =$ $0, S_0 = 0, E_A = H_{\mu}$, and so Eq. (11) may be rewritten in the form

$$\log A = \log(N_0 q^2 a \sqrt{2E_A} / \pi k \sqrt{m}) + E_A / 2.3 kT. \quad (12)$$

Experimental values of log A and E_A are presented in Figs. 4, 5, and 6 and compared with the dependence specified by Eq. (12) for silver, copper, thallium, indium, and cadmium salts (see Fig. 4), for alkali metals



FIG. 4. Prefactor vs activation energy for conductivity of silver, copper, thallium superionic conductors. The full circles correspond to hypothetical values for AgCl and AgBr crystals calculated assuming $n = N_0 =$ 10^{22} cm⁻³. The curve is plotted in accord with Eq. (12).

	$\log A$				$\log A$		
	E.	$(\mathbf{S} \cdot \mathbf{K})$			E.	$(\mathbf{S} \cdot \mathbf{K})$	
Substance	(eV)	(<u></u>)	Ref.	Substance	(eV)	(<u></u>)	Ref.
α-Ag₃SI	0.042	3.5	39	$Na_5YSi_4O_{12} (c)$	0.221	4,3	47
α-AgI	0.052	3.32	39	LiNa- β -Al ₂ O ₃	0.23	4.4	48
α-Ag ₂ Se	0.059	3.8	40	Na0.7Ga4.72Ti0.29O8	0.25	2.3	49
α -Ag ₂ S	0.066	3.02	40	$Li_N (\perp c)$	0.25	4.2	50
Ag ₄ KI,	0.07	3.0	41	Na _{0 75} K _{0 25} -B-Al ₂ O ₃	0.27	2.9	51
Ag ₄ RbI ₅	0.07	3.0	41	K-B-Al ₂ O ₃	0.28	3.6	42
Ag,Te	0.10	3.7	41	Na ₃ Zr ₂ Si ₂ PO ₁₂	0.30	4.4	52
a-Cu1 RbACles	0.104	4.0	41	$Na-\beta''-Al_2O_3$	0.33	6.6	42
$Cu_RbCl_(I_1, Cl_)$	0.117	3.2	41	Nan Kno-B-Al2O3	0.36	4.1	51
AgialisP207	0.143	5.2	41	α -Li ₂ SO ₄	0.36	4.7	14
AgeLWO	0.156	4.0	41	Ligeo ssMoo 1sO4	0.37	4.6	53
Ag-B-Al ₂ O ₂	0.16	3.0	42	LiGeo Moo 104	0.38	4.7	53
(CH ₁),NAg ₂ I ₂	0.16	5.0	41	Rb-B-Al-O	0.39	4.3	42
Ag-LPO.	0.165	37	41	Na «Ka «-B-Al-O	0.40	4.6	51
R-Ag-SI	0.17	35	41	Li Geor Moor O	0.42	4 5	53
Cu-Se	0.17	41	14	a-L i-NL	0.42	4 1	54
	0.174	3.2	14 A1	$N_2 \dots K_1 \dots R_1 A \downarrow O_1$	0.44	4.1	51
Ag I VO	0.174	3.4	<i>1</i> 1	K = 7n, $Sn = 0$	0.45	51	55
$\Lambda g_{14} \vee O_4$	0.174	J.4 4 4	41	I S NIDr	0.45	3.1	51
$A_2 - f(CH) = 0$	0.19	4.4	42		0.45	J.J 4 6	51
$Ag_{13}[(CH_3)_4N_{12}I_{15}]$	0.19	4.4	41	$NaK-\beta-Al_2O_3$	0.45	4.0	51
	0.203	5.0	43	$Na_2ZFID(PO_4)_3$	0.40	5.0	50
$(C_5H_5NH)Ag_{18}I_{23}$	0.21	4.1	41	Na ₆ CaP ₂ O ₉	0.40	5.4	5/
α -Cu ₂ S	0.25	5.1	41	α -LI ₁₃ N ₄ Br	0.4/	4.0	54
$Ag_{13}[(C_2H_5)_4N]_2I_{15}$	0.26	5.3	41	$Na_{1.8}Zr_{1.2}YD_{0.8}(PO_4)_3$	0.48	5.2	20
α -Cu _{1.6} Kb ₄ I ₇	0.29	7.5	41	$K_{1.12}Ta_{1.12}W_{0.88}O_6$	0.48	5.3	45
α-CuPb ₃ Br ₇	0.34	1.4	44	$L_{1.8}N_{0.4}Cl_{0.6}$	0.49	4.9	54
Ag ₂ Hgl ₄	0.37	5.3	39	$Na_{1.5}Zr_{1.5}Yb_{0.5}(PO_4)_3$	0.50	5.0	56
TITaWO ₆	0.38	4.5	45	β -Li ₅ NI ₂	0.50	5.0	54
$Tl_{1.9}Ta_{1.9}W_{0.1}O_6$	0.39	6.0	45	$Na_{2.5}Zr_{0.5}Yb_{1.5}(PO_4)_3$	0.50	5.3	56
Tl _{1.95} Ta _{1.95} W _{0.05} O ₆	0.40	5.7	45	$Na_{1.7}Al_{1.7}Si_{0.3}O_4$	0.50	6.8	57
Ag ₂ CdI ₄	0.43	6.0	39	$Na_{0.2}K_{0.8}-\beta-Al_2O_3$	0.52	4.9	51
Ag ₂ ZnI ₄	0.44	5.6	39	K _{0.8} Li _{0.2} -β-Al ₂ O ₃	0.52	5.1	48
$Tl_{1.25}Ta_{1.25}W_{0.75}O_6$	0.50	6.3	45	Li4Ge0.55M00.45O4	0.52	5.2	53
$Tl_{1.3}Ta_{1.3}W_{0.7}O_6$	0.50	6.4	45	K _{0.7} Mg _{0.35} Sn _{0.65} O ₂	0.52	5.7	55
$Tl_{1.6}Ta_{1.6}W_{0.4}O_6$	0.50	6.8	45	K _{0.7} Ca _{0.35} Sn _{0.65} O ₂	0.54	5.1	55
$Tl_{1.5}Ta_{1.5}W_{0.5}O_6$	0.52	6.8	45	Na _{1.6} Al _{1.6} Si _{0.4} O ₄	0.55	7.5	57
$Tl_{1.75}Ta_{1.75}W_{0.25}O_6$	0.55	7.0	45	β -Na ₃ Sc ₂ (PO ₄) ₃	0.55	7.9	46
$Tl_{1.8}Ta_{1.8}W_{0.2}O_6$	0.57	7.1	45	$Li_{14}Zn(GeO_4)_4$	0.56	5.9	50
Cd-β-Al ₂ O ₃	0.61	7.0	42	Li _{3.6} Si _{0.6} P _{0.4} O ₄	0.57	6.0	50
Cu ₂ HgI ₄	0.62	6.9	39	$K_{1.3}Ta_{1.3}W_{0.7}O_6$	0.57	6.0	45
In ₂ ZnI ₄	0.75	6.8	39	$Na_{2.6}Zr_{0.4}Yb_{1.6}(PO_4)_3$	0.58	6.0	56
Tl₂ZnI₄	0.87	5.1	39	NaAlSiO₄	0.58	6.1	57
In ₂ CdI ₆	0.95	7.4	39	Na _{1.3} Al _{1.3} Si _{0.7} O ₄	0.58	6.7	57
Tl ₂ ZnBr ₄	1.03	7.7	39	Na1.4Al1.4Si0.6O4	0.59	7.3	57
Na-β-Al ₂ O ₃	0.15	3.6	42	$K_{1.4}Ta_{1.4}W_{0.6}O_6$	0.60	6.1	45
Κ- β″-Al ₂ O ₃	0.15	4.2	42	Li7TaO6	0.60	6.3	58
$Na_3Sc_2(PO_4)_3$	0.19	2.4	46	$Na_{2.8}Zr_{0.2}Yb_{1.8}(PO_4)_3$	0.61	6.2	57
$Na_5YSi_4O_{12} (\perp c)$	0.203	3.6	47	$Na_{1.2}Al_{1.2}Si_{0.80}O_4$	0.61	7.6	58

TABLE III

Experimental Values of E_A and log A in Superionic Conductors

		log A				log A	
	EA	$(\mathbf{S} \cdot \mathbf{K})$			E_{A}	$(\mathbf{S} \cdot \mathbf{K})$	
Substance	(eV)	(<u>-cm</u>)	Ref.	Substance	(ev)	(<u>cm</u>)	Ref.
Li ₇ NbO ₆	0.64	5.7	55	α-TlBiF₄	0.38	4.0	1
$K_{0.72}In_{0.72}Zr_{0.28}O_2$	0.65	6.6	55	Pb _{0.88} Th _{0.12} F _{2.24}	0.38	4.3	62
K _{0.72} In _{0.72} Hf _{0.28} O ₂	0.67	7.5	50	Pb _{0.73} Bi _{0.27} F _{2.27}	0.38	4.5	61
Li ₅ AlO ₄	0.68	8.1	57	$Pb_{0.88}Zr_{0.12}F_{2.24}$	0.38	4.8	62
Na ₂ SiAlO _{4.5}	0.68	8.4	45	$Pb_{0.81}Th_{0.19}F_{2.38}$	0.38	4.9	62
$K_{1.5}Ta_{1.5}W_{0.5}O_6$	0.69	6.3	55	KBiF₄	0.38	5.0	63
$K_{0.72}In_{0.72}Sn_{0.28}O_2$	0.69	7.0	55	$Pb_{0.82}Sb_{0.18}F_{2.18}$	0.39	5.1	61
β-Li ₁₃ N₄Br	0.73	5.9	54	$Pb_{0.86}Zr_{0.14}F_{2.28}$	0.40	4.9	62
Na2.9Zr0.1Yb1.9(PO4)	0.77	7.7	56	Pb _{0.92} Zr _{0.08} F _{2.16}	0.41	5.2	61
LiAlSiO4	0.78	4.4	50	Pb _{0.63} Sb _{0.37} F _{2.37}	0.42	5.9	61
Li ₃ N (c)	0.79	8.2	50	β-PbSnF₄	0.42	6.8	60
Li ₆ In ₂ O ₆	0.80	6.4	58	Pb _{0.8} Bi _{0.2} F _{2.2}	0.43	5.0	61
Li _{9.1} N _{2.7} I	0.80	6.8	54	$Pb_{0.9}Sb_{0.1}F_{2.1}$	0.43	5.3	61
$Na_{1,12}Ta_{1,12}W_{0.88}O_6$	0.80	6.6	45	$Pb_{0.4}Bi_{0.6}F_{2.2}$	0.44	5.2	63
Li ₁₁ N ₃ Cl ₂	0.83	6.1	54	$Pb_{0.95}Zr_{0.05}F_{2.1}$	0.44	5.3	62
$Na_{1.8}Ta_{1.8}W_{0.2}O_6$	0.85	7.6	45	Pb _{0.82} Bi _{0.18} F _{2.18}	0.45	5.0	61
$Na_{1.4}Ta_{1.4}W_{0.60}O_6$	0.86	7.7	45	Pb _{0.77} Th _{0.23} F _{2.46}	0.45	5.1	62
$Na_{1.62}Ta_{1.62}W_{0.38}O_6$	0.90	8.2	45	$Pb_{0.95}Th_{0.05}F_{2.1}$	0.45	5.2	62
Li ₈ SnO ₆	0.91	8.5	58	LaF ₃	0.46	5.3	64
Li ₆ Ge ₂ O ₇	0.91	6.4	58	Na _{0.4} Bi _{0.6} F _{2.2}	0.46	5.8	63
Na _{0.9} In _{0.9} Sn _{0.1} O ₂	0.93	4.9	55	$Pb_{0.82}Zr_{0.18}F_{2.36}$	0.48	5.4	62
Li₄GeO₄	0.94	6.1	53	Pb _{0.59} Sb _{0.41} F _{2.41}	0.48	6.4	61
NaInO ₂	1.09	5.6	55	Pb _{0.97} Sb _{0.03} F _{2.03}	0.49	5.4	61
_				$Pb_{0.9}Bi_{0.1}F_{2.1}$	0.51	5.4	61
α-PbSnF₄	0.17	3.5	60	$Na_{0.38}Bi_{0.62}F_{2.24}$	0.51	6.3	63
Pb _{0.73} Sb _{0.27} F _{2.27}	0.30	4.4	61	Na _{0.36} Bi _{0.64} F _{2.28}	0.53	6.4	63
$Pb_{0.9}Th_{0.1}F_{2.2}$	0.35	4.5	62	Pb _{0.75} Th _{0.25} F _{2.5}	0.55	5.8	62
Pb _{0.85} Th _{0.15} F _{2.30}	0.35	4.6	62	Na _{0.33} Th _{0.67} F _{2.34}	0.56	6.5	63
$Pb_{0.8}Sb_{0.2}F_{2.2}$	0.35	4.9	61	Pb _{0.97} Bi _{0.03} F _{2.03}	0.57	5.9	61
Pb _{0.68} Sb _{0.32} F _{2.27}	0.36	5.2	61	Pb ₃ ZrF ₁₀	0.62	5.9	63
RbBiF₄	0.37	4.5	63	NaBiF₄	0.65	5.9	63
$Pb_{0.9}Zr_{0.1}F_{2.2}$	0.37	4.8	62	Na _{0.3} Bi _{0.7} F _{2.4}	0.65	7.3	63

TABLE III—Continued

ion SIC (Fig. 5), and for fluorine ion solid electrolytes (Fig. 6). It is interesting that values of log A for AH and for AgCl, AgBr calculated from experimental data of the conductivity of doped crystals assuming n= N_0 are in rather good accord with Eq. (12). Experimental data for most of the SIC with $E_A > 0.4 \pm 0.1$ eV are in fair agreement with the calculated relation. In the range of activation energies $0.3 < E_A < 0.5$ eV the prefactor A falls sharply with decreasing E_A and at $E_A = 0.3$ eV it assumes a value characteristic for jonic melts. From the above as well as from previous studies the following mechanism for ion migration in SIC may be suggested.

(i) In solid electrolytes with $E_A > 0.4 \pm 0.1 \text{ eV}$ the ion transport mechanism is likely to be similar to that which is characteristic of classical ionic crystals and involves the simple jump process. The values of S_{μ} and ν_0 are close to that of AH, for which relations (9) and (10) apply.

(ii) The apparent decrease in the prefactor A in SIC for which $0.3 < E_A < 0.5$ eV may be explained in terms of two main



FIG. 5. The calculated in accord with Eq. (12) (the curve) and experimentally observed (the points) compensation law for alkali-metal conducting SIC. Full circles are hypothetical values calculated assuming $n = N_0 = 10^{22}$ cm⁻³ for NaF, NaCl, NaBr, and NaI crystals.

causes. First, the migration entropy decreases to zero as a result of positional disordering of mobile sublattice ions, whenever ions can stay in interstitials for a relatively long time. Second, the jump attempt frequency decreases due to the strong anharmonicity of ion vibrations.

(iii) SIC with $E_A < 0.3$ eV are not different from ionic melts in conductivity parameters. For a description of the mechanism



FIG. 6. The compensation law for fluorine-conducting SIC. The curve is plotted in accord with Eq. (12).



FIG. 7. The distribution curves of the number of SIC with a given value of E_A vs E_A for Ag⁺, Cu⁺, Tl⁺, In⁺, Cd²⁺ ion conducting (1), alkali ion conducting (2), F⁻ ion conducting (3) ionic solids. The analyzed data are those presented in Table III.

of migration in these materials a stochastic model may be used (65).

Thus the CL allows one to follow the consequent stages of melting of the mobile ion sublattice. In a large number of compounds only a partially fused sublattice occurs. As a sharp change of energy parameters takes place at melting, a similar change must be observed in E_A values. In Fig. 7 the number of compounds in a certain interval of activation energy vs E_A are plotted for SIC of different types. These variations were obtained by means of histogram analysis for the E_A interval from 0 to 0.8 eV in steps of 0.05 eV for all compounds in Table III. The E_A curve yields a rather acute minimum at $0.3 < E_A < 0.4 \text{ eV}$ i.e., there seems to be an analog of the "forbidden gap" for $E_{\rm A}$ values of SIC.

Conclusion

The CL in conductivity of AH type crystals and of SIC is investigated. The CL in AH type crystals may be explained by assuming similar ones exist in the defect formation process (Eq. (8)) as well as in defect mobility (Eq. (9)), with the isokinetic temperatures 2.8×10^3 and 2.1×10^3 K, respectively. It is also shown that the values of ν_h determined by Eq. (10) are likely to be preferable to the Debye frequency. The dependence between log A and E_A exhibits an anomalous decrease in log A values for low E_A which seems to be caused by the melting of the mobile ion sublattice. The above relations can be employed for the prediction of transport properties of ionic solids (66, 67), and could be of advantage for further understanding of the ion transport mechanisms in solids.

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